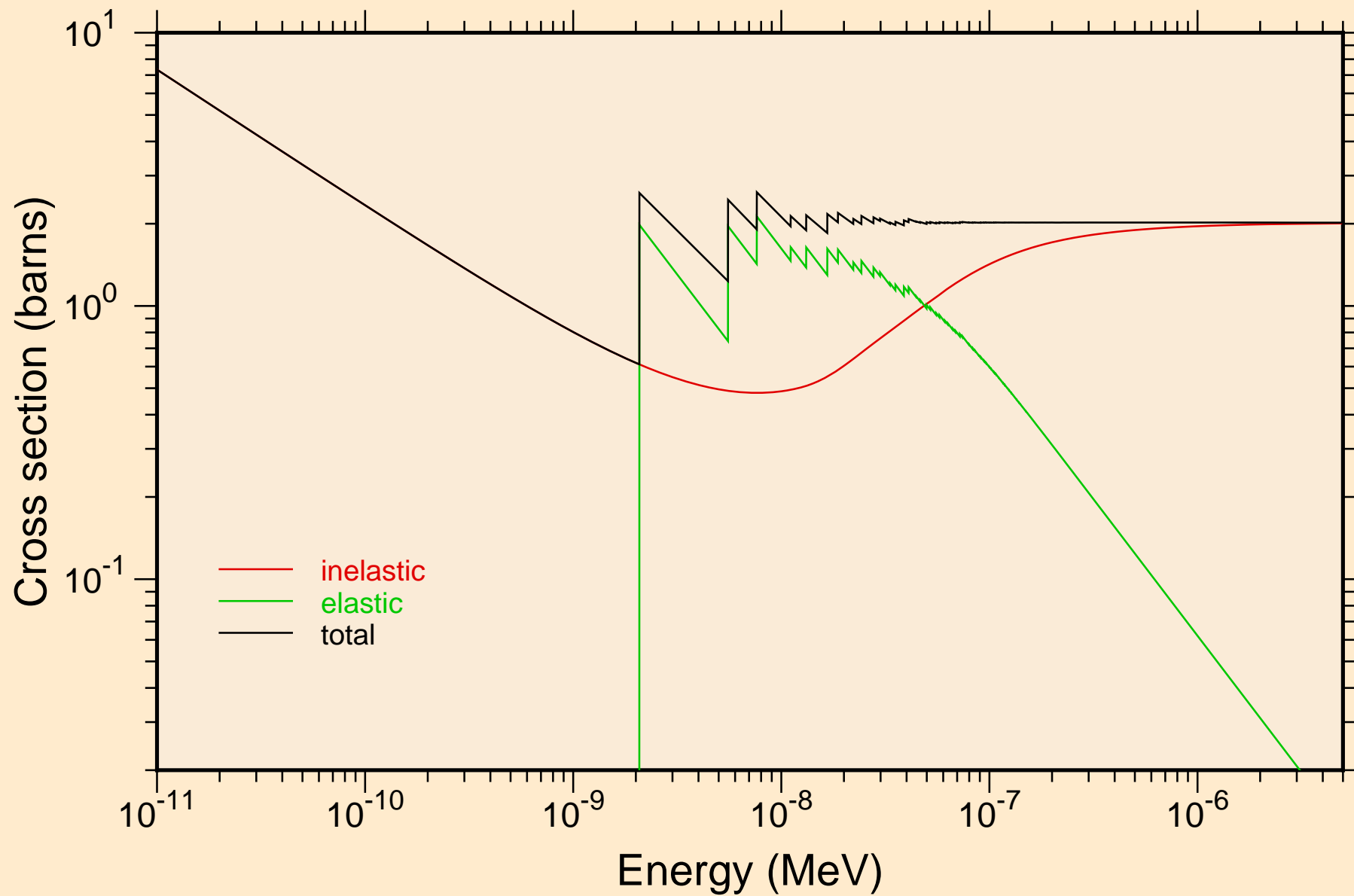
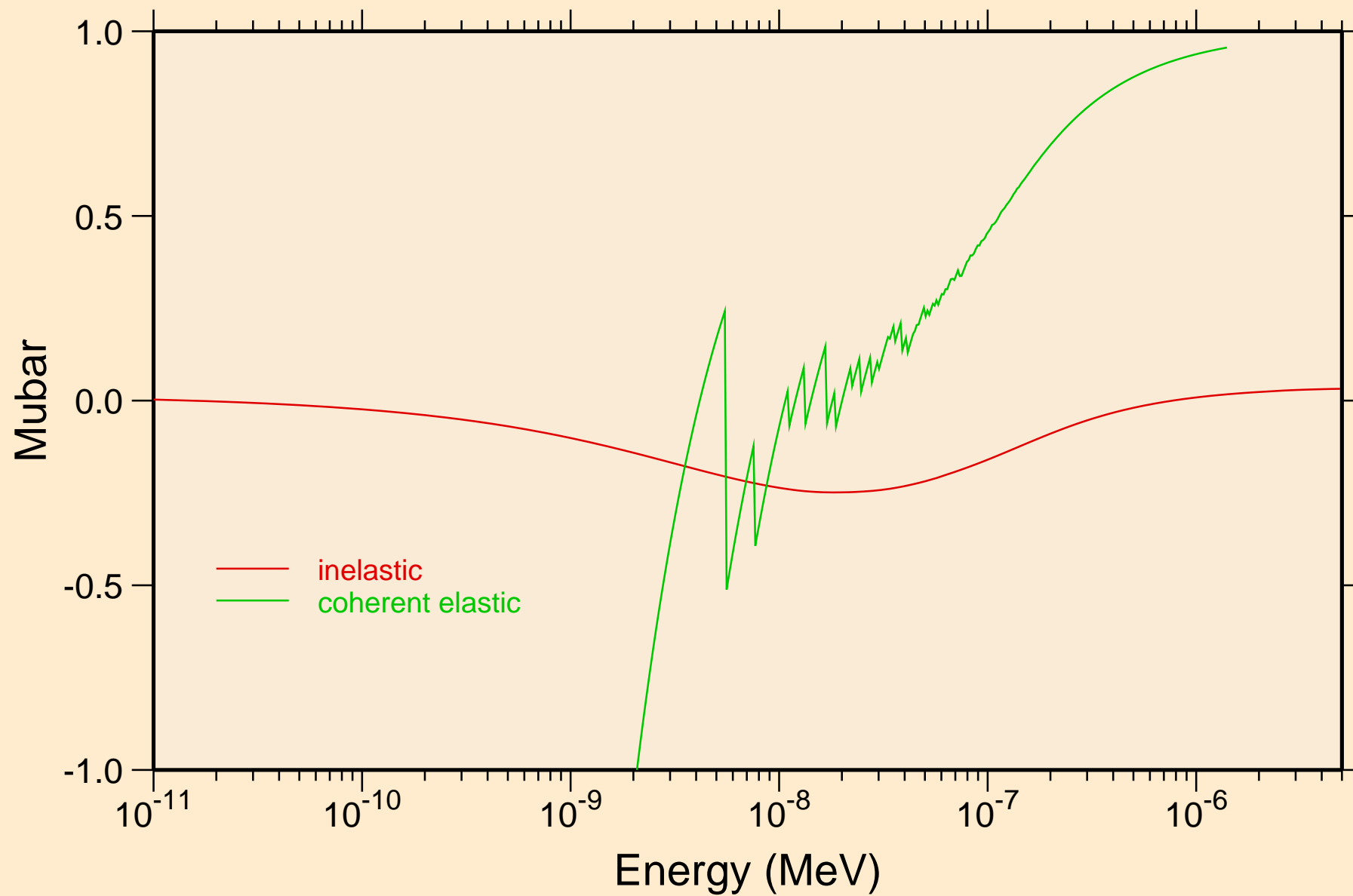


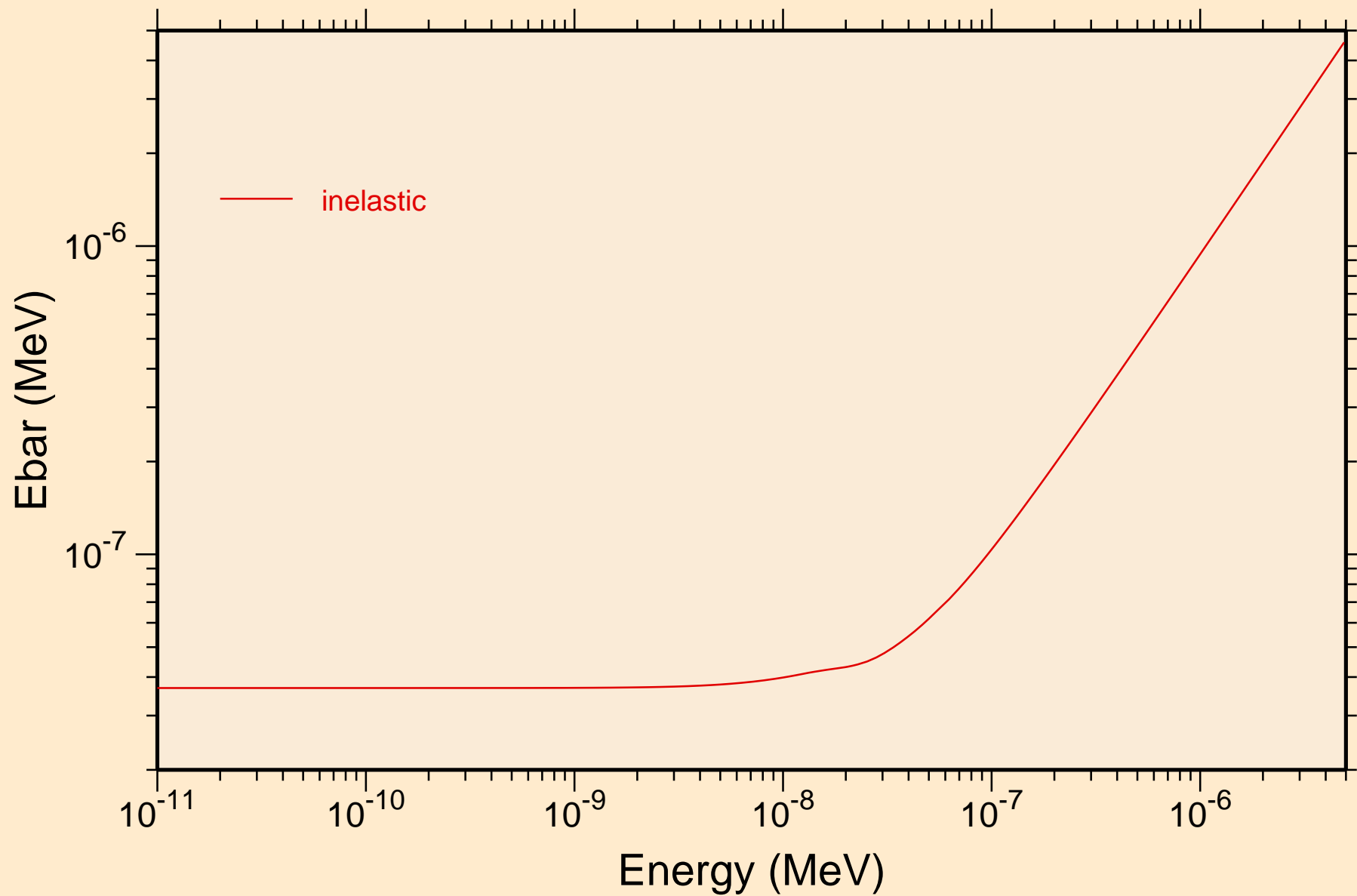
SI-SI\_SG227\_SILICON @ 800.00K  
Thermal cross sections



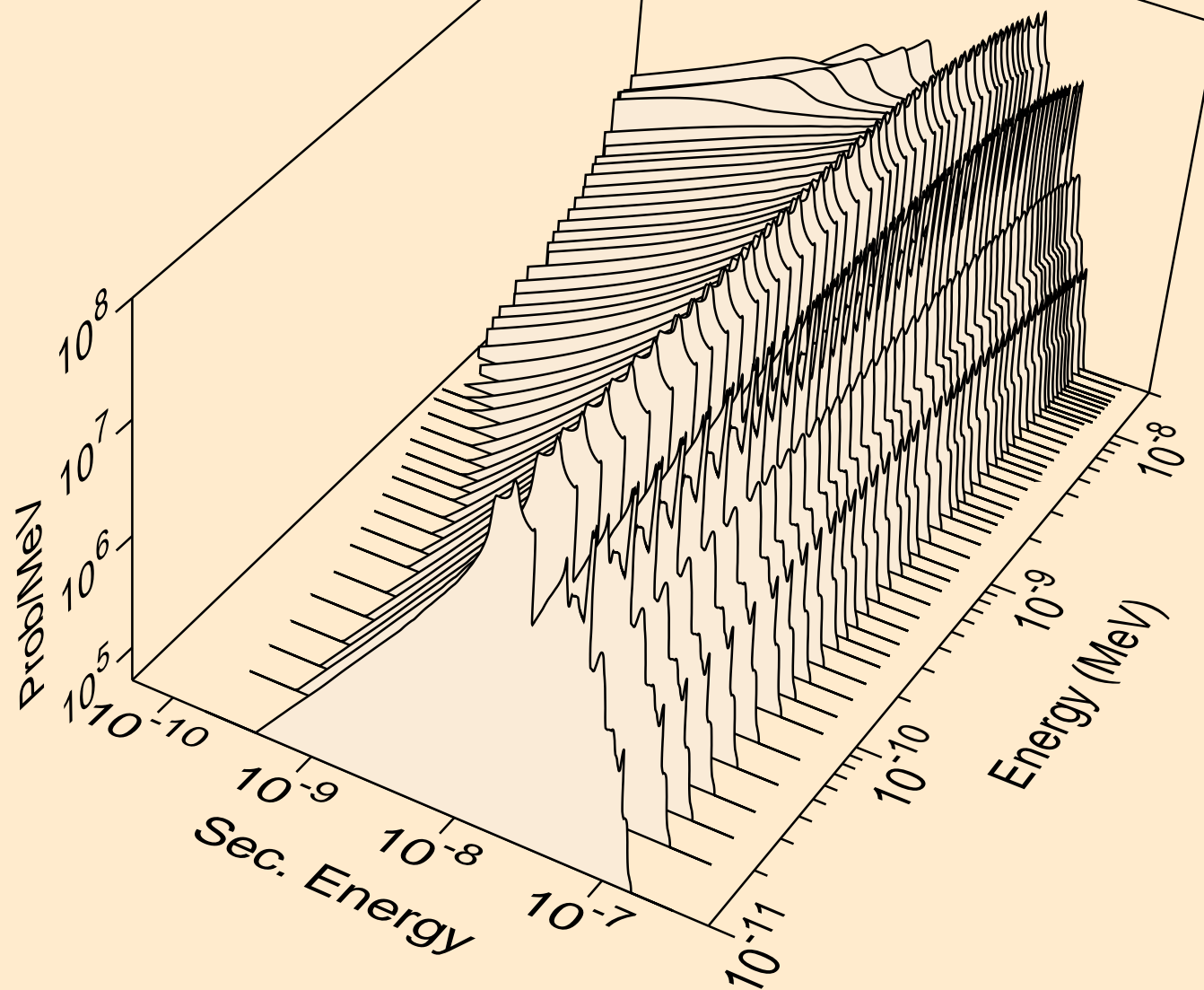
SI-SI\_SG227\_SILICON @ 800.00K  
Thermal mubar



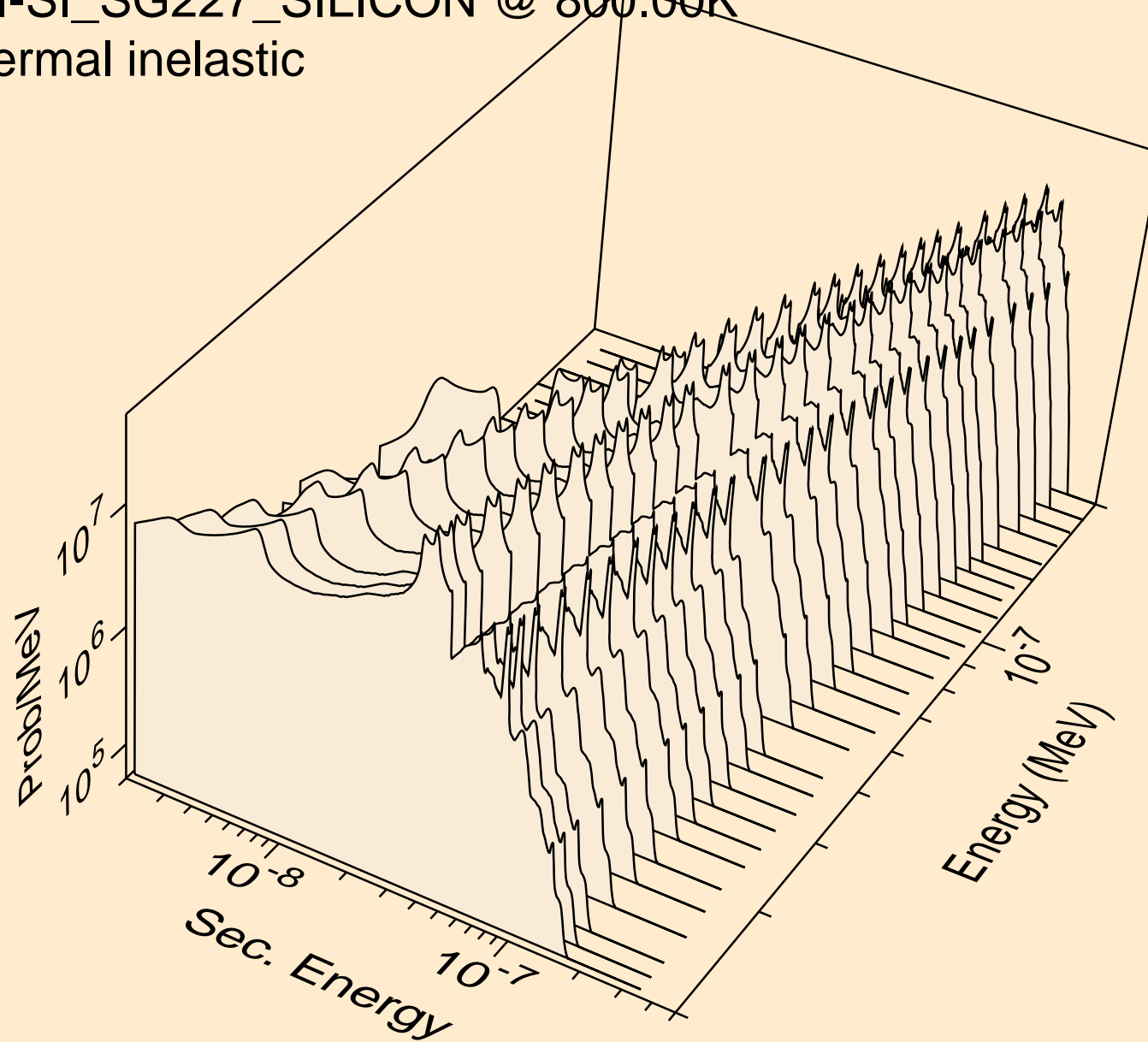
SI-SI\_SG227\_SILICON @ 800.00K  
Thermal ebar



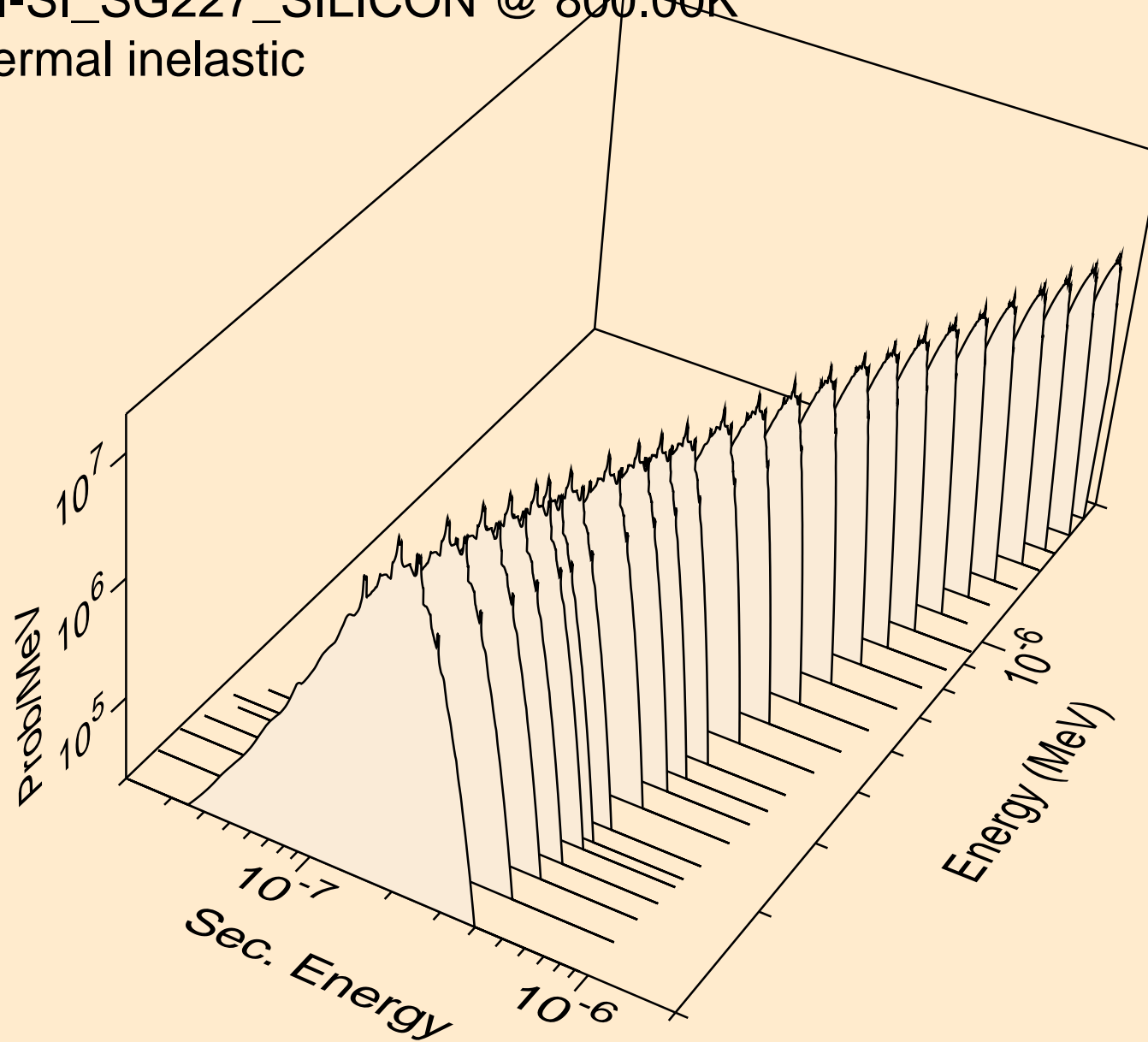
SI-SI\_SG227\_SILICON @ 800.00K  
thermal inelastic



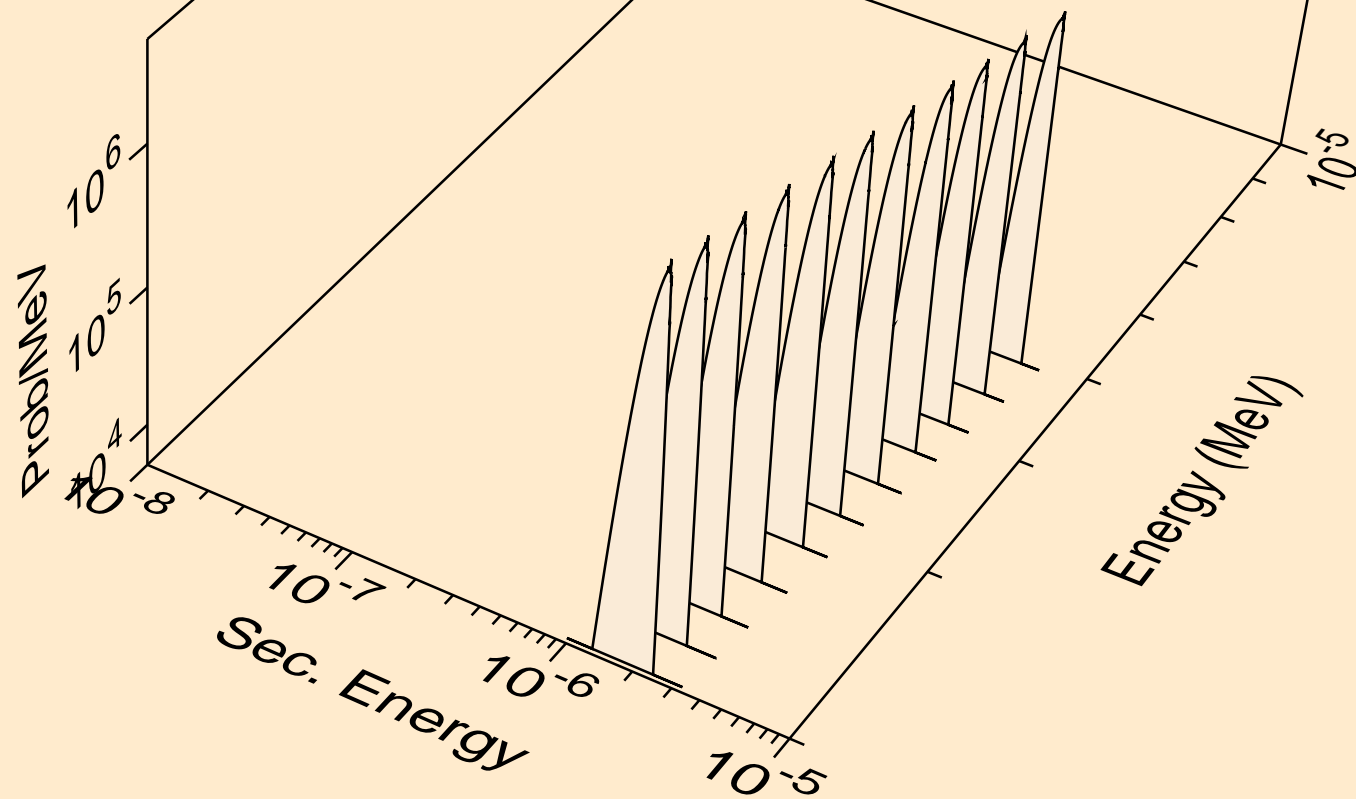
SI-SI\_SG227\_SILICON @ 800.00K  
thermal inelastic



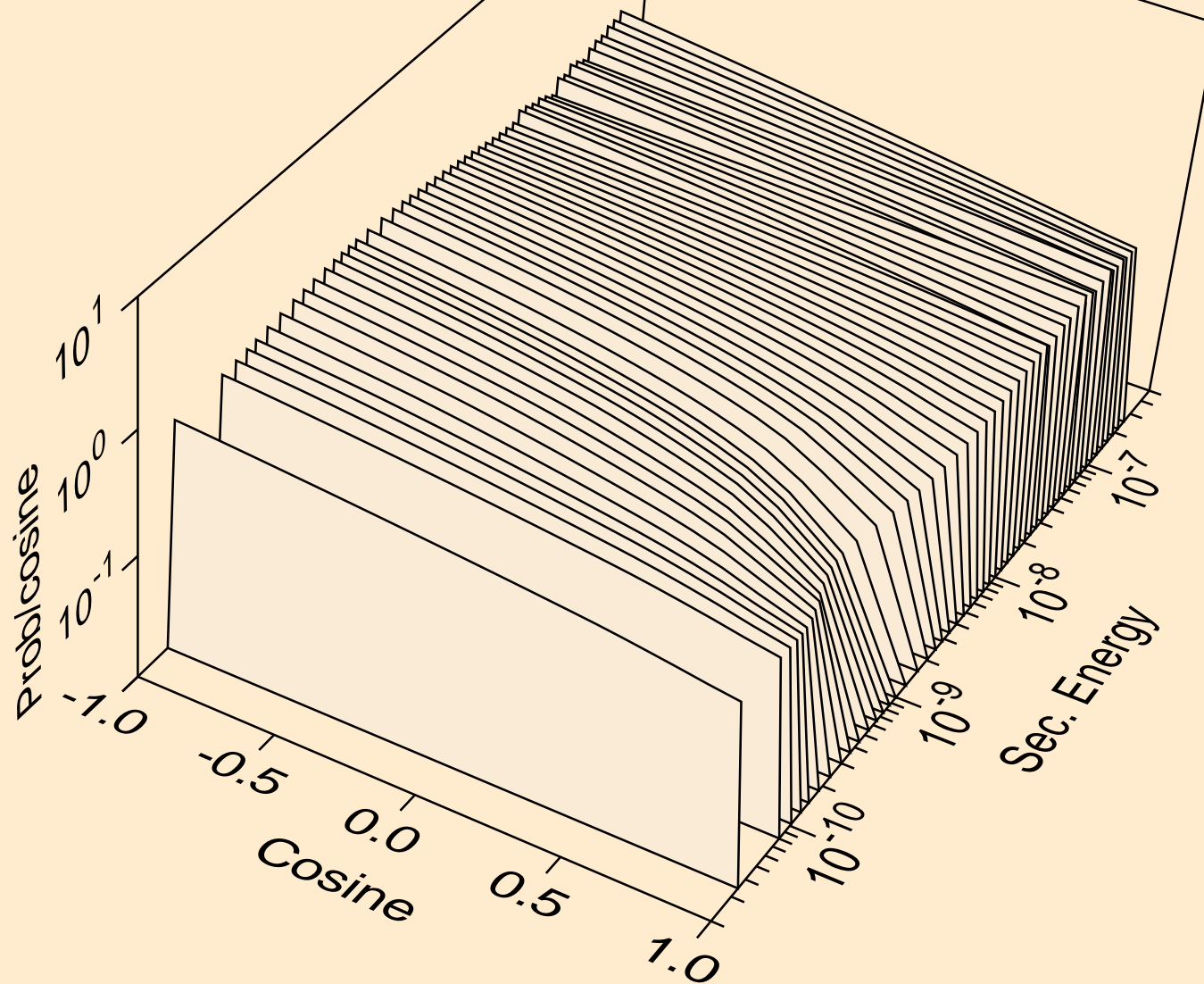
SI-SI\_SG227\_SILICON @ 800.00K  
thermal inelastic



SI-SI\_SG227\_SILICON @ 800.00K  
thermal inelastic

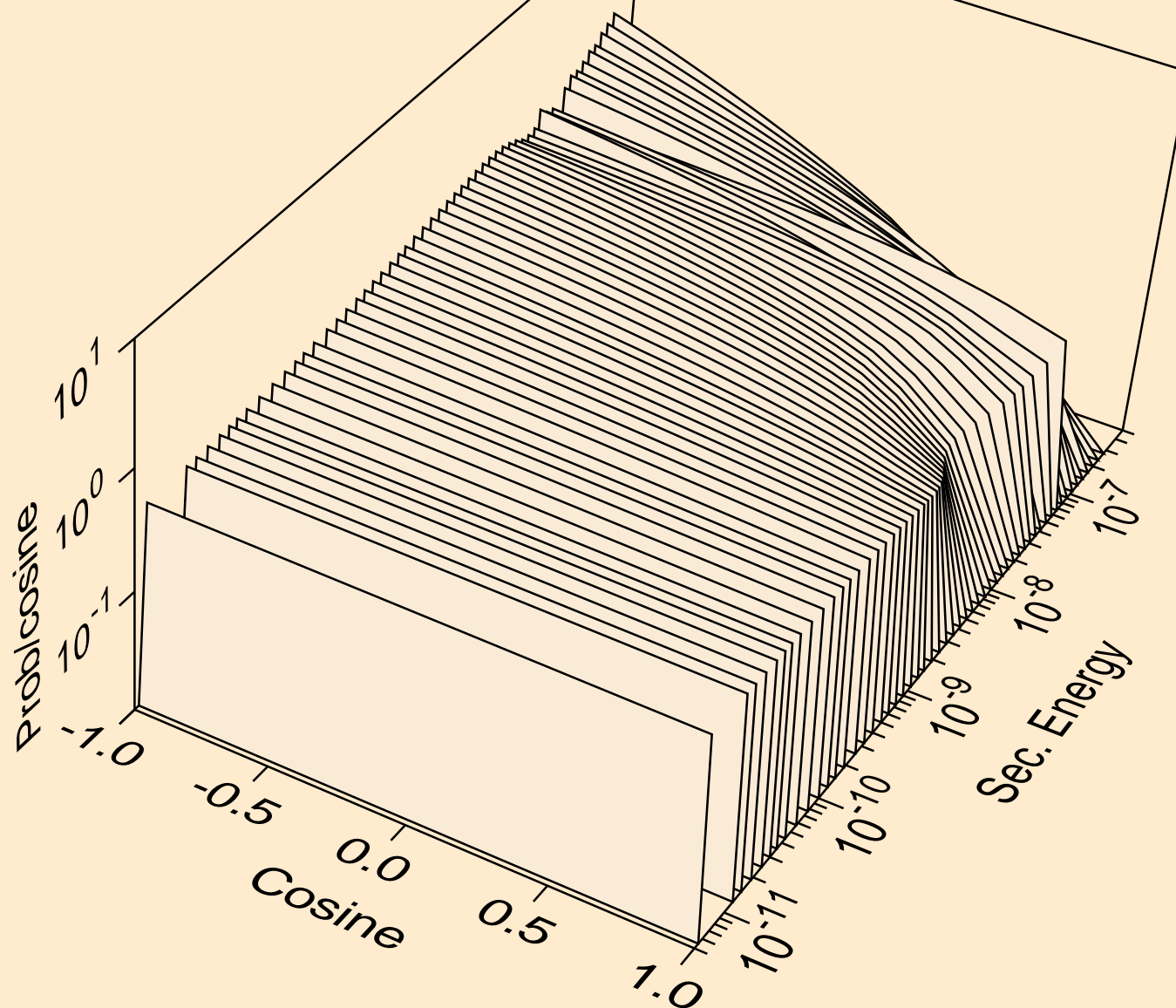


SI-SI\_SG227\_SILICON @ 800.00K  
thermal inelastic for e= 1.012E-09 MeV

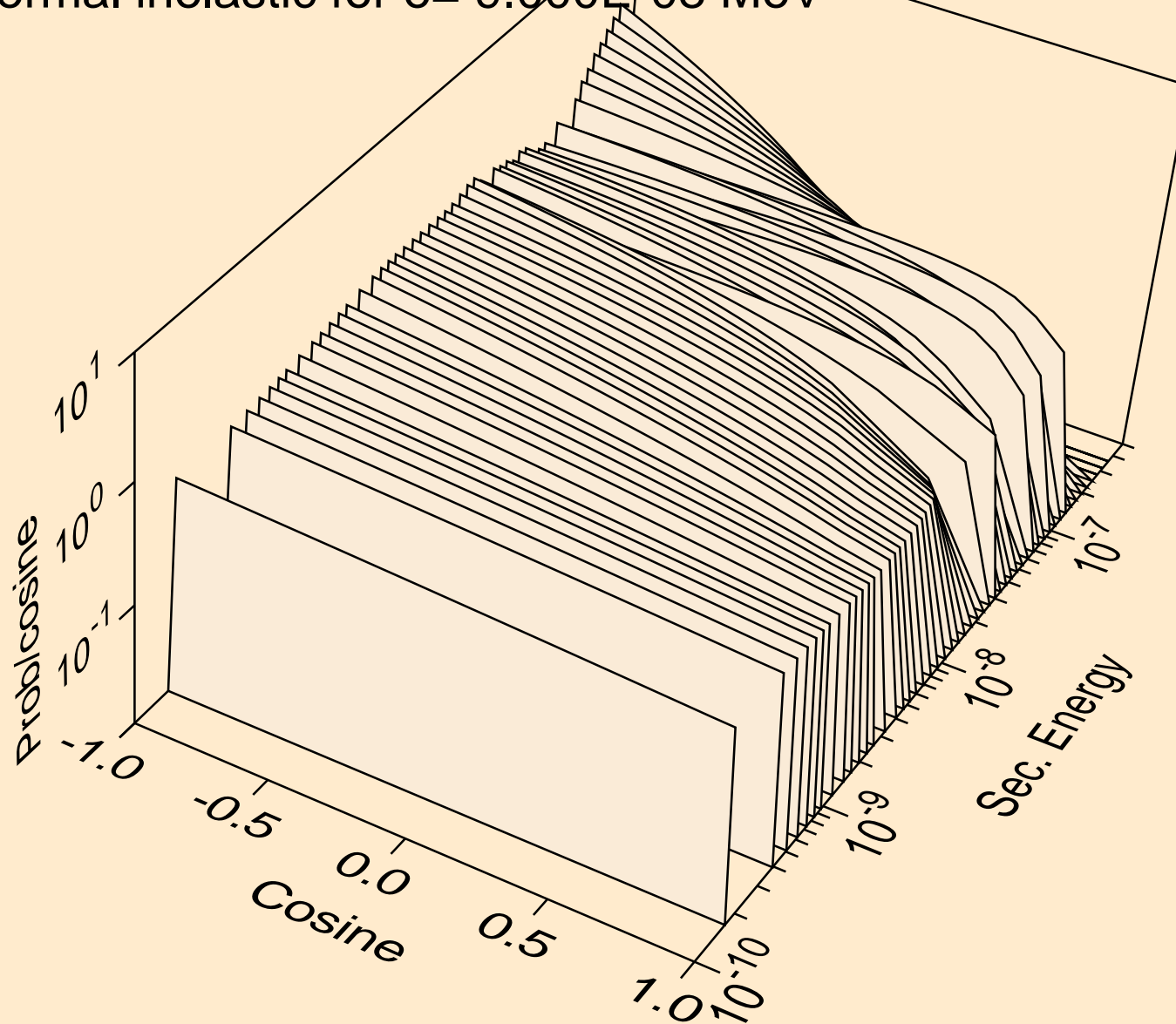




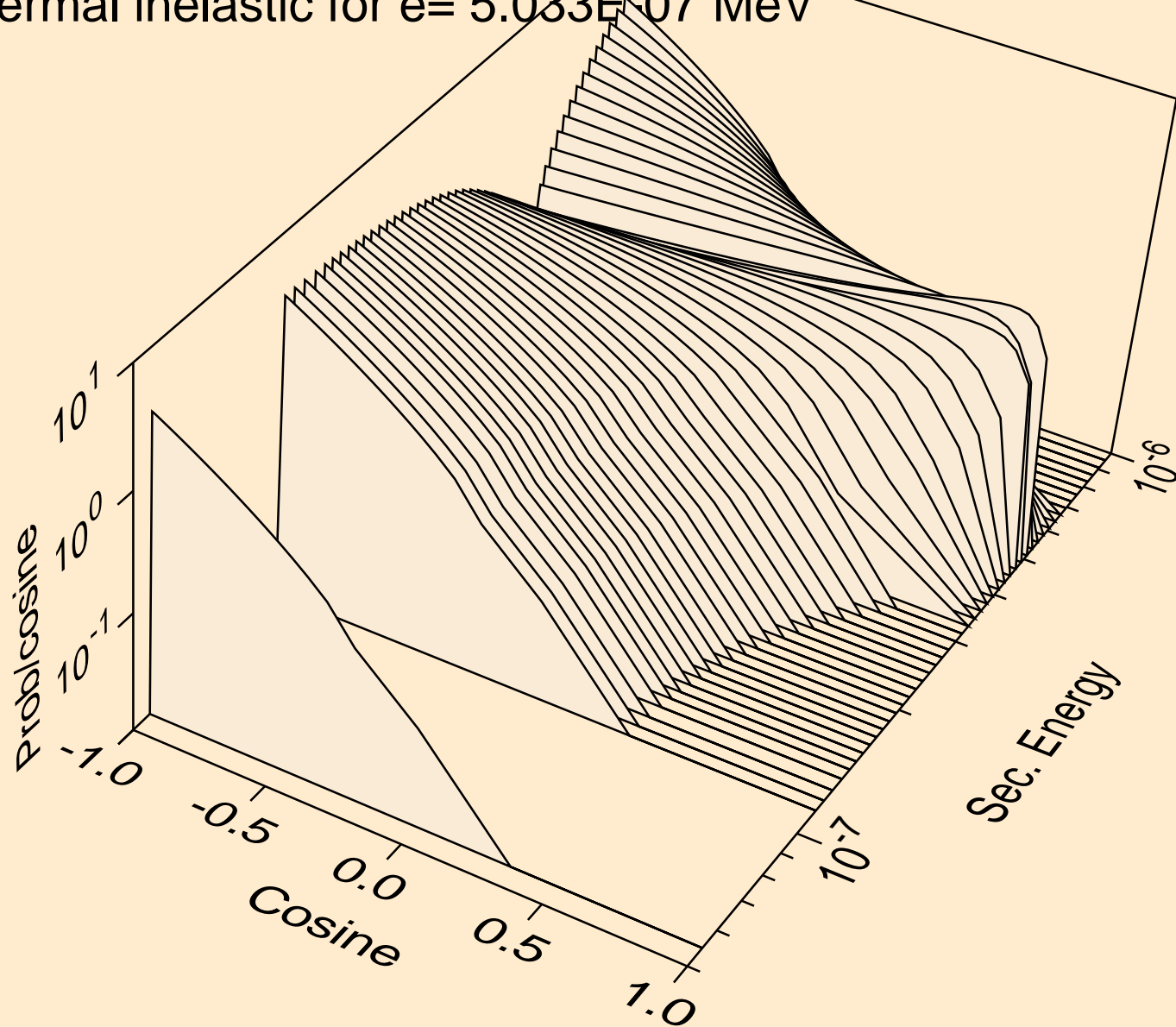
SI-SI\_SG227\_SILICON @ 800.00K  
thermal inelastic for e= 1.417E-08 MeV



SI-SI\_SG227\_SILICON @ 800.00K  
thermal inelastic for e= 9.000E-08 MeV



SI-SI\_SG227\_SILICON @ 800.00K  
thermal inelastic for  $e = 5.033 \times 10^{-7}$  MeV



SI-SI\_SG227\_SILICON @ 800.00K  
thermal inelastic for e= 4.070E-06 MeV

